

Silicon NPN Power Transistors

2SC1113

DESCRIPTION

- With TO-66 package
- High current capacity
- Wide area of safe operation

APPLICATIONS

- For power amplifier and switching applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

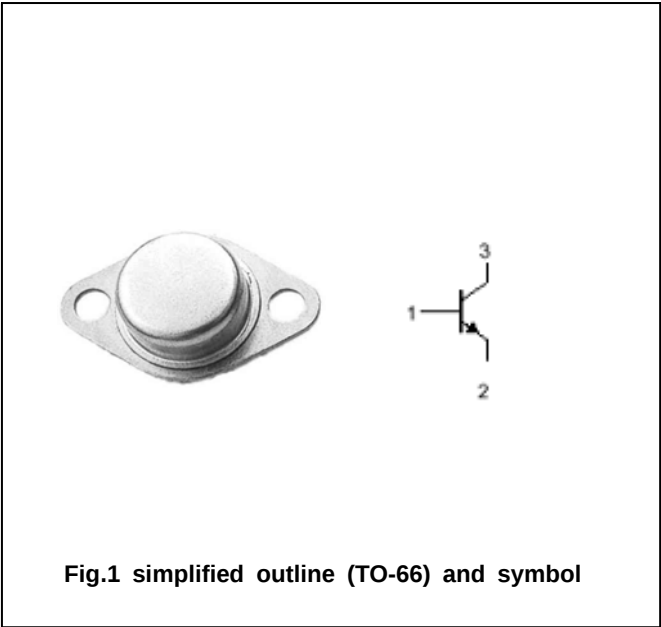


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	120	V
V _{CEO}	Collector-emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
P _T	Total power dissipation	T _C =25℃	40	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

Silicon NPN Power Transistors**2SC1113****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =25mA ; I _B =0	100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =0.5A			1.5	V
I _{CEO}	Collector cut-off current	V _{CE} =120V; I _B =0			10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μ A
h _{FE}	DC current gain	I _C =5A ; V _{CE} =4V	30			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V	10			MHz

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PACKAGE OUTLINE

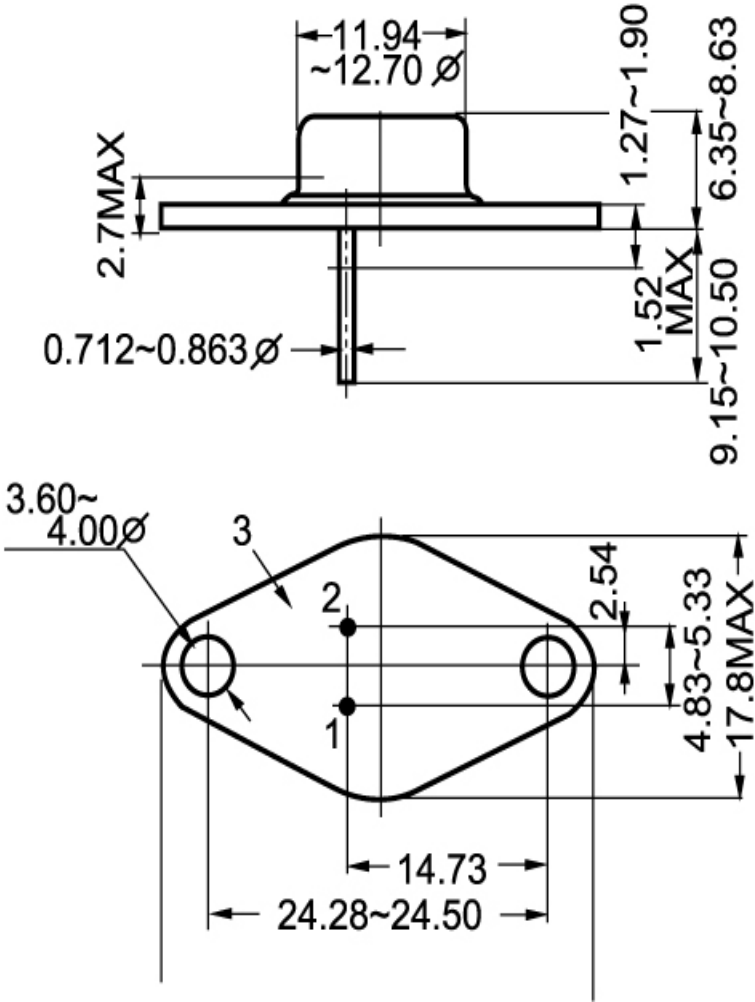


Fig.2 Outline dimensions